

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

<b>Applicant:</b>	Jiang	<b>Art Unit:</b>	3766
<b>Serial No.:</b>	10/629,291	<b>Examiner:</b>	Gedeon, Brian T
<b>Filed:</b>	07/28/2003		
<b>Docket No.:</b>	A329-USA		
<b>For:</b>	Material and Methods of Forming Yttria-Stabilized Zirconia to Minimize Low-Temperature Degradation		

**DECLARATION UNDER 37 CFR 1.132**

Sir:

I, Guangqiang Jiang, declare that:

1. I am an employee of The Alfred E. Mann Foundation for Scientific Research, Inc. and I am a named inventor in the present application, U.S. Patent Application Number 10/629,291, "Material and Methods of Forming Yttria-Stabilized Zirconia to Minimize Low-Temperature Degradation", filed on 07/28/2003.

2) I am skilled in the art of ceramic materials processing and selections.

3) I hold six US patents and have worked as a materials scientist for 8 years, having a Ph.D. in Biomedical Engineering with an emphasis in materials from the University of Southern California.


4) To my knowledge, 'sintering' is distinguished from hot isostatic pressing. Both are densification methods for ceramic materials which involve diffusion. "Sintering" is heating a mass of fine particles for a prolonged time at a temperature below the melting point, usually at ambient pressure, to cause agglomeration. "Hot isostatic pressing" is a process involving simultaneous application of heat and pressure to a material that is contained in a sealed flexible mold and is subjected to equal pressure from all directions while at a temperature high enough to cause densification.

5) The undersigned declares further that all statements made herein of their own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge

that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Respectfully submitted,

5/31/2008  
\_\_\_\_\_  
Date

  
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Guangqiang Jiang